

Title (en)

SEMICONDUCTOR MEMORY ELEMENT, PRODUCTION METHOD AND OPERATIONAL METHOD

Title (de)

HALBLEITERSPEICHERELEMENT, VERFAHREN ZUR HERSTELLUNG UND VERFAHREN ZUM BETRIEB

Title (fr)

ELEMENT DE MEMOIRE A SEMI-CONDUCTEURS, SON PROCEDE DE FABRICATION ET PROCEDE PERMETTANT SON FONCTIONNEMENT

Publication

EP 1423880 A1 20040602 (DE)

Application

EP 02760145 A 20020902

Priority

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- DE 10143235 A 20010904

Abstract (en)

[origin: WO03026014A1] A semiconductor memory element (200) comprising a substrate, wherein a source area (201) and a drain area (202) are formed; a floating gate (203) which is electrically insulated from the substrate; a tunnel barrier arrangement (204) which enables the floating gate (203) to be charged or discharged, the conductivity of the channel between the source (201) and drain (202) area being modifiable by charging or discharging the floating gate; in addition to means which control transmission of the charge of the tunnel barrier arrangement and which have a source line (213) which is electroconductingly connected to the source area.

IPC 1-7

H01L 27/115; **H01L 29/788**; **H01L 29/51**; **H01L 21/8247**; **G11C 16/04**

IPC 8 full level

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CPC (source: EP US)

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Citation (search report)

See references of WO 03026014A1

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